TOSHIBA Field Effect Transistor Silicon N Channel MOS Type (U-MOSII)

# **TPC6201**

HDD Motor Drive Applications
Notebook PC Applications
Portable Equipment Applications

• Low drain-source ON resistance:  $RDS(ON) = 80 \text{ m}\Omega \text{ (typ.)}$ 

• High forward transfer admittance:  $|Y_{fs}| = 3.8 \text{ S (typ.)}$ 

• Low leakage current:  $I_{DSS} = 10 \mu A \text{ (max) (V}_{DS} = 30 \text{ V)}$ 

• Enhancement-model:  $V_{th}$  = 1.3 to 2.5 V ( $V_{DS}$  = 10 V,  $I_{D}$  = 1 mA)

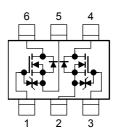
## **Maximum Ratings (Ta = 25°C)**

C	characteristics	Symbol	Rating	Unit	
Drain-source voltage		$V_{DSS}$	30	V	
Drain-gate vo	ltage (R <sub>GS</sub> = 20 kΩ)	$V_{DGR}$	30	V	
Gate-source	voltage	$V_{GSS}$	±20	٧	
Drain	DC (Note 1)	Ι <sub>D</sub>	2.5	Α	
current	Pulse (Note 1)	VDSS 30 VDGR 30 VGSS ±20 1) ID 2.5 1) IDP 10 PD (1) 0.9 PD (2) 0.76 PD (2) 0.31 PD (2) 0.31 PD (3) PD (4) 1.25 PD (5) EAR 0.16 Tch 150	ζ		
Drain power dissipation (t = 5 s) (Note 2a)	Single-device operation (Note 3a)	P <sub>D</sub> (1)	0.9	W	
	Single device value at dual operation (Note 3b)	P <sub>D</sub> (2)	0.76		
Drain power dissipation (t = 5 s) (Note 2b)	Single-device operation (Note 3a)	P <sub>D</sub> (1)	0.4	W	
	Single device value at dual operation (Note 3b)	P <sub>D</sub> (2)	0.31		
Single pulse a	ulse avalanche energy (Note 4) E <sub>AS</sub> 1.0		mJ		
Avalanche cu	rrent	I <sub>AR</sub>	1.25	Α	
Repetitive ava	alanche energy (Note 5)	E <sub>AR</sub>	0.16	mJ	
Channel temp	perature	T <sub>ch</sub>	150	°C	
Storage temp	erature range	T <sub>stg</sub>	-55 to 150	°C	

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Weight: 0.011 g (typ.)

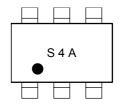
# **Circuit Configuration**



#### **Thermal Characteristics**

Characteristics		Symbol	Max	Unit	
Thermal Resistance (channel-to-ambient) (t = 5 s) (Note 2a)	Single-device operation (Note 3a)	R <sub>th (ch-a)</sub> (2)	139	°C/W	
	Single device value at dual operation (Note 3b)	R <sub>th (ch-a)</sub> (2)	165	C/VV	
Thermal Resistance (channel-to-ambient) (t = 5 s) (Note 2b)	(Note 3a		310	°C/W	
	Single device value at dual operation (Note 3b)	R <sub>th (ch-a)</sub> (2)	400	C/VV	

# Marking (Note 6)



Note: (Note 1), (Note 2), (Note 3), (Note 4), (Note 5), (Note 6) Please see next page.

This transistor is an electrostatically sensitive device. Please handle it with caution.

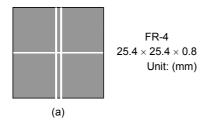
## **Electrical Characteristics (Ta = 25°C)**

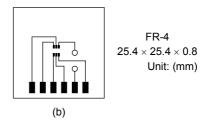
Characteristics		Symbol	Test Condition	Min	Тур.	Max	Unit
Gate leakage current		I <sub>GSS</sub>	$V_{GS} = \pm 16 \text{ V}, V_{DS} = 0 \text{ V}$	_	_	±10	μΑ
Drain cut-OFF current		I <sub>DSS</sub>	V <sub>DS</sub> = 30 V, V <sub>GS</sub> = 0 V	_	_	10	μА
Drain-source breakdown voltage		V <sub>(BR) DSS</sub>	I <sub>D</sub> = 10 mA, V <sub>GS</sub> = 0 V 30		_	_	V
		V <sub>(BR) DSX</sub>	$I_D = 10 \text{ mA}, V_{GS} = -20 \text{ V}$	15	_	_	v
Gate threshold vo	oltage	V <sub>th</sub>	V <sub>DS</sub> = 10 V, I <sub>D</sub> = 1 mA	1.3	_	2.5	V
Drain-source ON resistance		R <sub>DS</sub> (ON)	$V_{GS} = 4.5 \text{ V}, I_D = 1.3 \text{ A}$	_	128	145	mO
		R <sub>DS (ON)</sub>	$V_{GS} = 10 \text{ V}, I_D = 1.3 \text{ A}$	_	80	95	mΩ
Forward transfer admittance		Y <sub>fs</sub>	V <sub>DS</sub> = 10 V, I <sub>D</sub> = 1.3 A	1.25	3.8	_	S
Input capacitance		C <sub>iss</sub>	V <sub>DS</sub> = 10 V, V <sub>GS</sub> = 0 V, f = 1 MHz	_	170	_	pF
Reverse transfer capacitance		C <sub>rss</sub>		_	25	_	
Output capacitance		Coss		_	40	_	
Switching time	Rise time	t <sub>r</sub>	VGS 0 V	_	2.4	_	ns
	Turn-ON time	t <sub>on</sub>		_	8	_	
	Fall time	t <sub>f</sub>		_	2	_	
	Turn-OFF time	t <sub>off</sub>	$V_{DD} \simeq 15 \text{ V}$ Duty $\leq 1\%$ , $t_W = 10 \mu\text{s}$		11	_	
Total gate charge (gate-source plus gate-drain)		Qg	V <sub>DD</sub> ≈ 24 V, V <sub>GS</sub> = 10 V,	_	4.7	_	
Gate-source charge		Q <sub>gs</sub>	$I_D = 2.5 \text{ A}$	_	3.4	_	nC
Gate-drain ("miller") charge		Q <sub>gd</sub>		_	1.3	_	

# **Source-Drain Ratings and Characteristics (Ta = 25°C)**

Characteristics		Symbol	Test Condition	Min	Тур.	Max	Unit
Pulse drain reverse current	(Note 1)	I <sub>DRP</sub>	_	_	_	10	Α
Forward voltage (diode)		$V_{DSF}$	$I_{DR} = 2.5 \text{ A}, V_{GS} = 0 \text{ V}$			-1.2	V

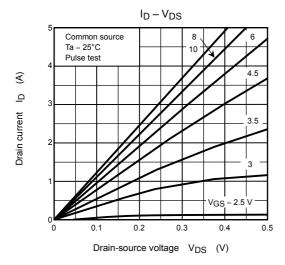
- Note 1: Please use devices on condition that the channel temperature is below 150°C.
- Note 2: (a) Device mounted on a glass-epoxy board (a) (t = 5 s)
  - (b) Device mounted on a glass-epoxy board (b) (t = 5 s)

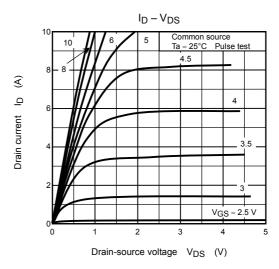


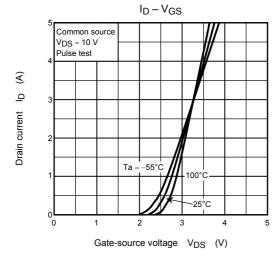


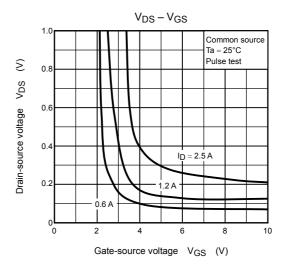
- Note 3: (a) Single-device operation; values of P<sub>D</sub> (1) and R<sub>th (ch-a)</sub> (1) for a single device during single-device operation
  - (b) Dual operation; values of  $P_D$  (2) and  $R_{th\ (ch-a)}$  (2) for a single device during dual operation
- Note 4:  $V_{DD} = 24$  V,  $T_{ch} = 25$ °C (initial), L = 0.5 mH,  $R_G = 25$   $\Omega$ ,  $I_{AR} = 1.25$  A
- Note 5: Repetitive rating; pulse width limited by maximum channel temperature
- Note 6: Black round marking "•" locates on the left lower side of parts number marking "S4A" indicates terminal No.1.

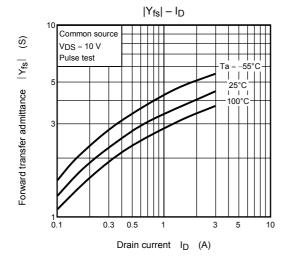
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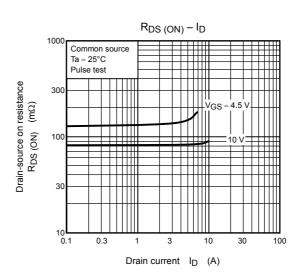




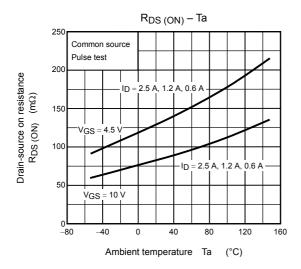


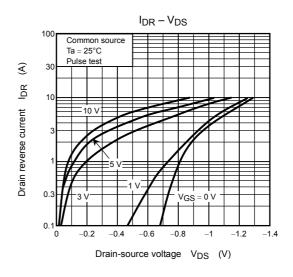


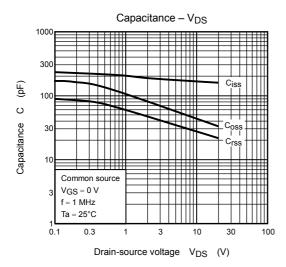


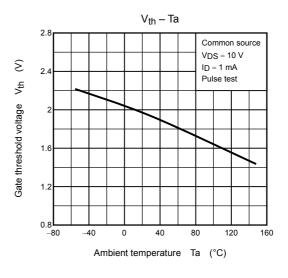


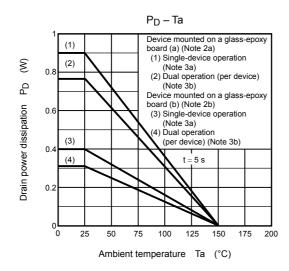
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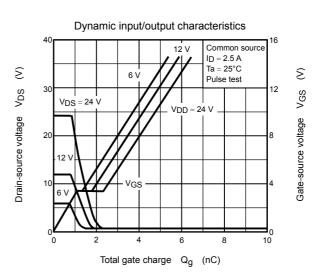


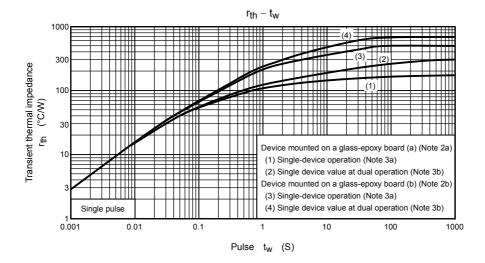


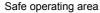


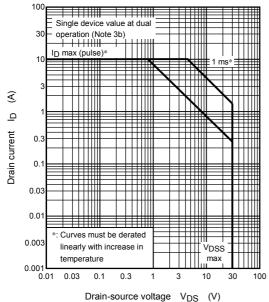












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